

GP20A - GP20M AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V CURRENT: 2.0 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

Case: DO-15

Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208

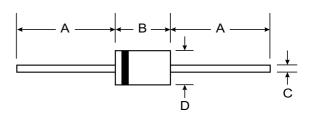
Polarity: Cathode Band

• Weight: 0.40 grams (approx.)

Mounting Position: AnyMarking: Type Number







DO-15							
Dim	Min	Max					
Α	25.40	_					
В	5.50	7.62					
С	0.686	0.889					
D	2.60	3.60					
All Dimensions in mm							

Maximum Ratings and Electrical Characteristics T_A = 25°C unless otherwise specified

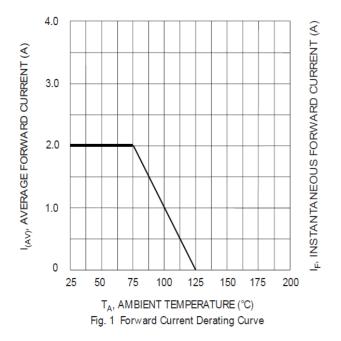
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

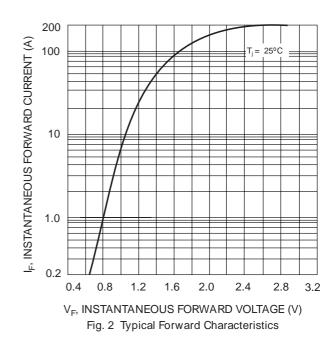
Characteristic	Symbol	GP20A	GP20B	GP20D	GP20G	GP20J	GP20K	GP20M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T _A = 75°C	lo	2.0						А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I FSM	70					А		
Forward Voltage $@I_F = 2.0A$	VFM	1.0					V		
Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 100^{\circ}C$	lгм	5.0 50					μΑ		
Typical Junction Capacitance (Note 2)	Cj	20						pF	
Typical Thermal Resistance Junction to Ambient (Note 1)	$R_{ heta}$ JA	40						K/W	
Operating Temperature Range	Tj	-65 to +125						°C	
Storage Temperature Range	Тѕтс	TsTG -65 to +150			0			°C	

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

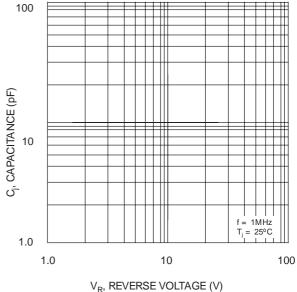






200 (¥)
100 Ti = 25°C
Pulse width = 300µs
1.0 10 100

NUMBER OF CYCLES AT 60Hz
Fig. 3 Maximum Non-Repetitive Surge Current



V_R, REVERSE VOLTAGE (V) Fig. 4 Typical Junction Capacitance